DATA SHEET



GaAs HBT INTEGRATED CIRCUIT

μ PG2301TQ

POWER AMPLIFIER FOR Bluetooth [™] Class 1

DESCRIPTION

The μPG2301TQ is GaAs HBT MMIC for power amplifier which were developed for Bluetooth Class 1.

This device realizes high efficiency, high gain and high output power by using InGaP HBT. This device is housed in a 10-pin plastic TSON package. And this package is able to high-density surface mounting.

FEATURES

Operation frequency : f_{opt} = 2 400 to 2 500 MHz (2 450 MHz TYP.)
 Supply voltage : V_{CC1, 2} = V_{bias} = 2.7 to 3.6 V (3.3 V TYP.)

• Control voltage : Vcont = 0 to 3.6 V (2.5 V TYP.)

: Venable = 0 to 3.1 V (2.9 V TYP.)

• Circuit current : Icc = 120 mA TYP. @ Vcc1, 2 = Vbias = 3.3 V, Vcont = 2.5 V, Venable = 2.9 V, Pin = +4 dBm

Maximum power : Pout(MAX.) = +23 dBm TYP.@ Vcc1, 2 = Vbias = 3.3 V, Vcont = 2.5 V, Venable = 2.9 V, Pin = +4 dBm
 Gain Control Range : GCR = 23 dB TYP.@ Vcc1, 2 = Vbias = 3.3 V, Vcont = 0 to 2.5 V, Venable = 2.9 V, Pin = +4 dBm

Power gain : G_P = 23 dB TYP.(Reference value)
 High efficiency : PAE = 50% TYP.(Reference value)

· Shut down function

• High-density surface mounting :10 pin plastic TSON package (2.4 × 2.55 × 0.6 mm)

APPLICATION

- Power Amplifier for Bluetooth Class 1 etc.
- Wireless LAN etc.

ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
μPG2301TQ-E1	10-pin plastic TSON	2301	Embossed tape 8 mm wide Pin 5, 6 face the perforation side of the tape Qty 3 kpcs/reel

Remark To order evaluation samples, contact your nearby sales office.

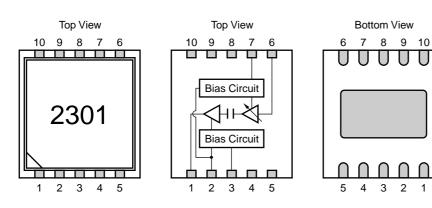
Part number for sample order: μPG2301TQ

Caution Electro-static sensitive devices

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.



PIN CONNECTIONS AND INTERNAL BLOCK DIAGRAM



Pin No.	Pin Name
1	OUTPUT/ Vcc2
2	Venable
3	V _{bias}
4	GND
5	Vcc1
6	INPUT
7	Vcont
8	N.C.
9	GND
10	GND

Bottom View

UUUU

2 3

ABSOLUTE MAXIMUM RATINGS (Unless otherwise specified, TA = +25°C)

Parameter	Symbol	Ratings	Unit
Supply Voltage	Vcc _{1,2}	5.0	V
	V _{bias}		
Control Voltage	V _{cont}	3.6	V
	Venable		
Circuit Current	Icc	400	mA
Control Current	Icont	0.5	mA
	lenable		
Power Dissipation	Po	700 Note	mW
Operating Ambient Temperature	TA	-40 to +85	°C
Storage Temperature	Tstg	-55 to +150	°C
Input Power	Pin	+10	dBm

Note Mounted on double copper-clad $50 \times 50 \times 1.6$ mm epoxy glass PWB, T_A = +85°C

RECOMMENDED OPERATING RENGE ($T_A = +25$ °C)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Operating Frequency	f _{opt}	2 400	2 450	2 500	MHz
Supply Voltage	VCC1,2	2.7	3.3	3.6	V
	V _{bias}				
Control Voltage	V _{cont}	0	2.5	3.6	V
	Venable	0	2.9	3.1	

ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, $T_A = +25$ °C, $V_{CC1, 2} = V_{bias} = 3.3$ V, f = 2 450 MHz, External input and output matching)

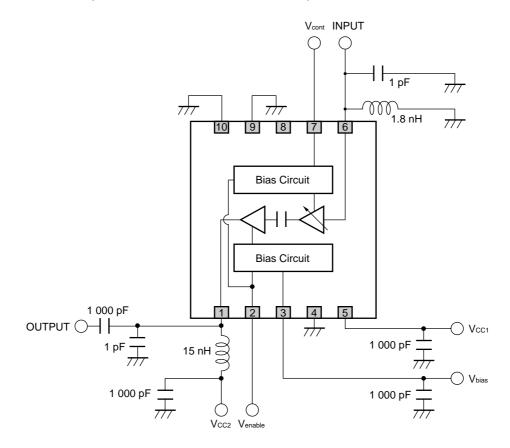
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	Icc	V _{cont} = 2.5 V, V _{enable} = 2.9 V, P _{in} = +4 dBm	110	120	130	mA
Shut Down Current	shut down	V _{cont} = 2.5 V, V _{enable} = 0 V, P _{in} = +4 dBm	_	0.1	1.0	μΑ
Output Power 1	Pout1	V _{cont} = 2.5 V, V _{enable} = 2.9 V, P _{in} = +4 dBm	+21	+23	+24.5	dBm
Output Power 2	P _{out2}	V _{cont} = 0 V, V _{enable} = 2.9 V, P _{in} = +4 dBm	_	0	+1	dBm
Gain Control Range	GCR	V _{cont} = 0 to 2.5 V, V _{enable} = 2.9 V, P _{in} = +4 dBm	20	23	_	dB

ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, $T_A = +25$ °C, $V_{CC1, 2} = V_{bias} = 3.3$ V, f = 2 450 MHz, External input and output matching)

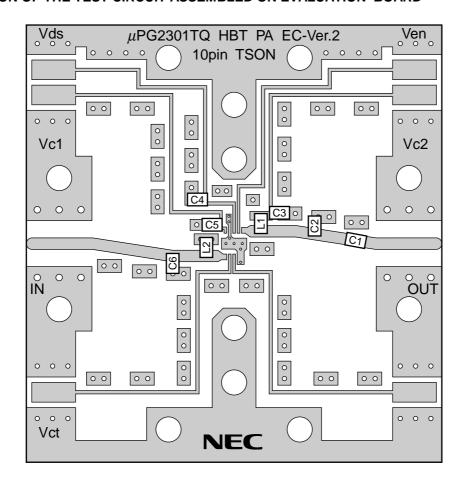
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Efficiency	PAE	$V_{cont} = 2.5 \text{ V}, V_{enable} = 2.9 \text{ V},$ $P_{in} = +4 \text{ dBm}$	-	50	-	%
Power Gain	G₽	V _{cont} = 2.5 V, V _{enable} = 2.9 V, P _{in} = -5 dBm	-	23	_	dB

EVALUATION CIRCUIT (Vcc1, 2 = Vbias = 3.3 V, f = 2 450 MHz)



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD

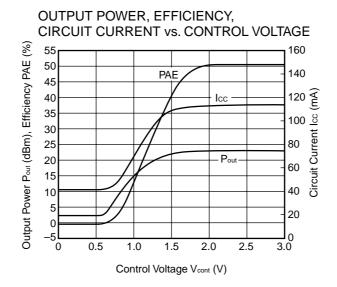


COMPONENT LIST

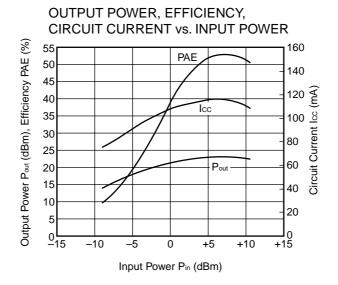
Symbol	Rating	Part Number	Munufacturer
C1, C3, C4, C5	1 000 pF	GRM39CH102J50	muRata
C2, C6	1 pF	GRM39CH010C50	muRata
L1	15 nH	TFL0816-15N	Susumu
L2	1.8 nH	TFL0816-1N8	Susumu

TYPICAL CHARACTERLISTICS

Condition: f = 2 450 MHz, Vcc1 = Vcc2 = Vbias = 3.3 V, Venable = 2.9 V, Pin = +4 dBm, External input and output matching



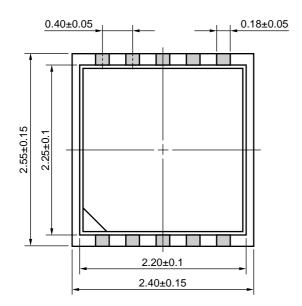
Condition: f = 2 450 MHz, Vcc1 = Vcc2 = Vbias = 3.3 V, Venable = 2.9 V, Vcont = 2.5 V, External input and output matching

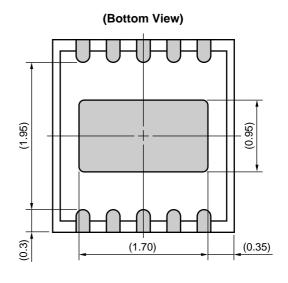


Remark The graphs indicate nominal characteristics.

PACKAGE DIMENSIONS

10-PIN PLASTIC TSON (UNIT: mm)







Note (): Reference value

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) Time at temperature of 200°C or higher Preheating time at 120 to 150°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 215°C or below : 25 to 40 seconds : 30 to 60 seconds : 3 times : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).

8

*μ*PG2301TQ

Bluetooth is a trademark owned by Bluetooth SIG, Inc., U.S.A.

- The information in this document is current as of February, 2002. The information is subject to change without notice. For actual design-in, refer to the latest publications of NEC's data sheets or data books, etc., for the most up-to-date specifications of NEC semiconductor products. Not all products and/or types are available in every country. Please check with an NEC sales representative for availability and additional information.
- No part of this document may be copied or reproduced in any form or by any means without prior written consent of NEC. NEC assumes no responsibility for any errors that may appear in this document.
- NEC does not assume any liability for infringement of patents, copyrights or other intellectual property rights of
 third parties by or arising from the use of NEC semiconductor products listed in this document or any other
 liability arising from the use of such products. No license, express, implied or otherwise, is granted under any
 patents, copyrights or other intellectual property rights of NEC or others.
- Descriptions of circuits, software and other related information in this document are provided for illustrative
 purposes in semiconductor product operation and application examples. The incorporation of these
 circuits, software and information in the design of customer's equipment shall be done under the full
 responsibility of customer. NEC assumes no responsibility for any losses incurred by customers or third
 parties arising from the use of these circuits, software and information.
- While NEC endeavours to enhance the quality, reliability and safety of NEC semiconductor products, customers
 agree and acknowledge that the possibility of defects thereof cannot be eliminated entirely. To minimize
 risks of damage to property or injury (including death) to persons arising from defects in NEC
 semiconductor products, customers must incorporate sufficient safety measures in their design, such as
 redundancy, fire-containment, and anti-failure features.
- NEC semiconductor products are classified into the following three quality grades:
 - "Standard", "Special" and "Specific". The "Specific" quality grade applies only to semiconductor products developed based on a customer-designated "quality assurance program" for a specific application. The recommended applications of a semiconductor product depend on its quality grade, as indicated below. Customers must check the quality grade of each semiconductor product before using it in a particular application.
 - "Standard": Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
 - "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
 - "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

The quality grade of NEC semiconductor products is "Standard" unless otherwise expressly specified in NEC's data sheets or data books, etc. If customers wish to use NEC semiconductor products in applications not intended by NEC, they must contact an NEC sales representative in advance to determine NEC's willingness to support a given application.

(Note)

- (1) "NEC" as used in this statement means NEC Corporation, NEC Compound Semiconductor Devices, Ltd. and also includes its majority-owned subsidiaries.
- (2) "NEC semiconductor products" means any semiconductor product developed or manufactured by or for NEC (as defined above).

M8E 00.4-0110

NEC μ PG2301TQ

SAFETY INFORMATION ON THIS PRODUCT

_		
Cau	1111	۱n
vai	auv	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,

GaAs Products

The product contains gallium arsenide, GaAs.

GaAs vapor and powder are hazardous to human health if inhaled or ingested.

- Do not destroy or burn the product.
- Do not cut or cleave off any part of the product.
- Do not crush or chemically dissolve the product.
- Do not put the product in the mouth.

Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.

▶Business issue

NEC Compound Semiconductor Devices, Ltd.

5th Sales Group, Sales Division TEL: +81-3-3798-6372 FAX: +81-3-3798-6783 E-mail: salesinfo@csd-nec.com

NEC Compound Semiconductor Devices Hong Kong Limited

Hong Kong Head Office TEL: +852-3107-7303 FAX: +852-3107-7309
Taipei Branch Office TEL: +886-2-8712-0478 FAX: +886-2-2545-3859
Korea Branch Office TEL: +82-2-528-0301 FAX: +82-2-528-0302

NEC Electron Devices European Operations http://www.nec.de/

TEL: +49-211-6503-101 FAX: +49-211-6503-487

California Eastern Laboratories, Inc. http://www.cel.com/

TEL: +1-408-988-3500 FAX: +1-408-988-0279

▶Technical issue

NEC Compound Semiconductor Devices, Ltd. http://www.csd-nec.com/

Sales Engineering Group, Sales Division

E-mail: techinfo@csd-nec.com FAX: +81-44-435-1918